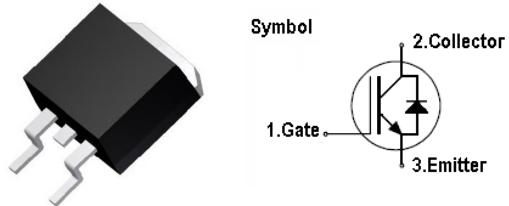


## IGBT in TO-263

### Features

- 650V 20A, V<sub>CE(sat)(typ.)</sub> = 1.70 V@20A
- Field Stop IGBT Technology
- 10µs Short Circuit Capability
- Square RBSOA
- Positive V<sub>CE</sub> (on) Temperature Coefficient



### Mechanical Data

- **Case:** TO-263 (plastic package). Lead free; RoHS compliant
- **Molding Compound Flammability Rating:** UL 94 V-0
- **Terminals:** High temperature soldering guaranteed: 260 °C/10 sec. at terminals

### Benefits

- High Efficiency for Motor Control
- Rugged Performance
- Excellent Current Sharing in Parallel Operation

### Applications

CREATEK's IGBTs offer lower losses and higher energy for application such as motor drive ,UPS, inverter and other soft switching applications.

### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	650	V
V <sub>GES</sub>	Gate-Emitter Voltage	±30	V
I <sub>C</sub>	Continuous Collector Current ( T <sub>C</sub> =25 °C)	40	A
	Continuous Collector Current ( T <sub>C</sub> =100°C)	20	A
I <sub>CM</sub>	Pulsed Collector Current (Note 1)	80	A
I <sub>F</sub>	Diode Continuous Forward Current ( T <sub>C</sub> =100 °C)	20	A
I <sub>FM</sub>	Diode Maximum Forward Current (Note 1)	80	A
t <sub>sc</sub>	Short Circuit Withstand Time	10	us
I <sub>sc</sub>	Short Circuit Current	150	A
P <sub>D</sub>	Maximum Power Dissipation ( T <sub>C</sub> =25 °C)	178	W
P <sub>D</sub>	Maximum Power Dissipation ( T <sub>C</sub> =100°C)	71	W
T <sub>J</sub>	Operating Junction Temperature Range	-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C

### Thermal Characteristics

Symbol	Parameter	Max.	Units
R <sub>th j-c</sub>	Thermal Resistance, Junction to case for IGBT	0.7	°C/W
R <sub>th j-c</sub>	Thermal Resistance, Junction to case for Diode	1.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	80	°C/W

**Electrical Characteristics** (TC=25°C unless otherwise noted)

<b>Symbol</b>	<b>Parameter</b>	<b>Test Conditions</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Units</b>
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250uA	650	-	-	V
I <sub>CES</sub>	Collector-Emitter Leakage Current	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	-	-	250	uA
I <sub>GES</sub>	Gate Leakage Current, Forward	V <sub>GE</sub> =30V, V <sub>CE</sub> = 0V	-	-	100	nA
	Gate Leakage Current, Reverse	V <sub>GE</sub> = -30V, V <sub>CE</sub> = 0V	-	-	-100	nA
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 250uA	4.0	-	5.5	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	V <sub>GE</sub> =15V, I <sub>C</sub> = 20A	-	1.70		V
Q <sub>g</sub>	Total Gate Charge	V <sub>CC</sub> =480V V <sub>GE</sub> =15V I <sub>C</sub> =20A	-	79		nC
Q <sub>ge</sub>	Gate-Emitter Charge		-	11		nC
Q <sub>gc</sub>	Gate-Collector Charge		-	43		nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>CC</sub> =400V V <sub>GE</sub> =15V I <sub>C</sub> =20A R <sub>G</sub> =10Ω Inductive Load	-	16	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	27	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	113	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	26	-	ns
E <sub>on</sub>	Turn-on Switching Loss		-	0.49	-	mJ
E <sub>off</sub>	Turn-off Switching Loss		-	0.31	-	mJ
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> =25V V <sub>GE</sub> =0V f = 1MHz	-	980	-	pF
C <sub>oes</sub>	Output Capacitance		-	130	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance		-	60	-	pF
R <sub>Gint</sub>	Integrated gate resistor	f=1MHz;Vpp=1V		2.30		Ω

**Electrical Characteristics of Diode** (TC=25°C unless otherwise noted)

<b>Symbol</b>	<b>Parameter</b>	<b>Test Conditions</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Units</b>
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> =20A	-	2.3		V
t <sub>rr</sub>	Diode Reverse Recovery Time	V <sub>CE</sub> = 400V I <sub>F</sub> = 20A dI <sub>F</sub> /dt = 500A/us	-	42		ns
I <sub>rrm</sub>	Diode peak Reverse Recovery Current		-	7.6		A
Q <sub>rr</sub>	Diode Reverse Recovery Charge		-	186		nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature

## Typical Characteristics

Fig 1. DC Collector current as a function of case temperature ( $V_{GE} \geq 15V$ ,  $T_j \leq 150^{\circ}C$ )

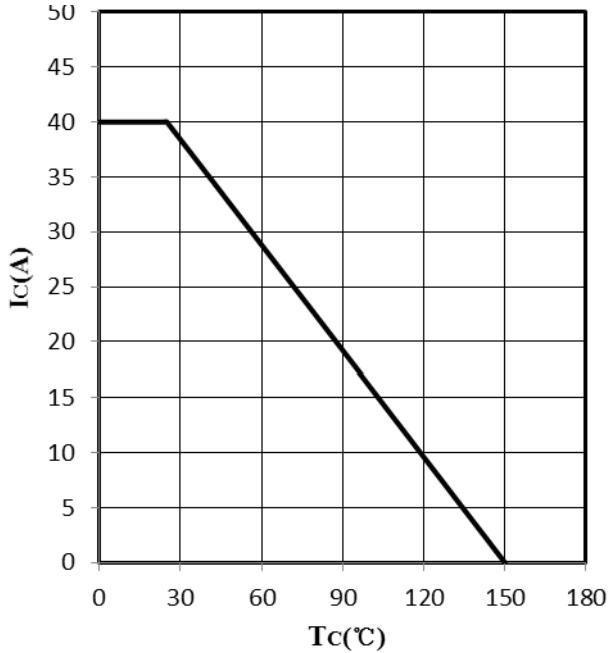


Fig 2. Power dissipation as a function of case temperature ( $T_j \leq 150^{\circ}C$ )

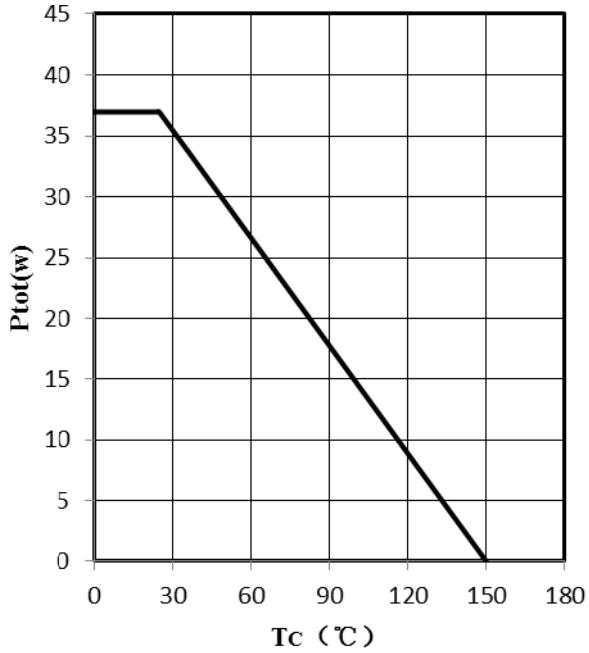


Fig 3. IGBT Forward safe operation area

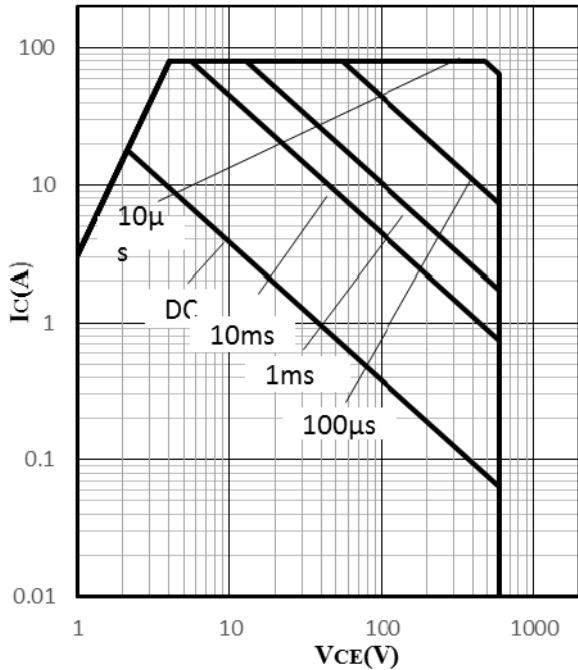
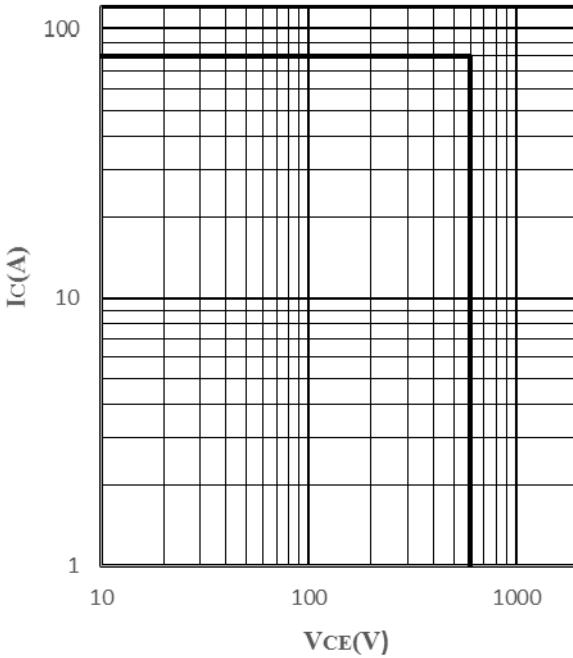


Fig 4. IGBT Reverse safe operation area



## Typical Characteristics

Fig 5. Typical output characteristic ( $T_j=25^\circ\text{C}$ )

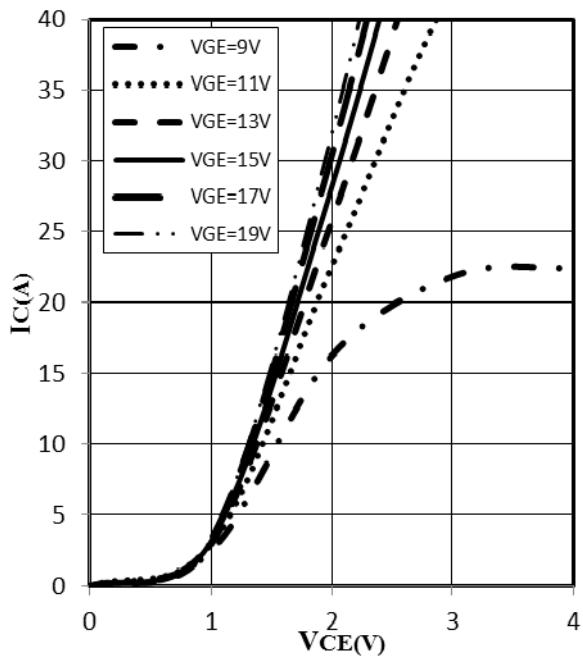


Fig 6. Typical output characteristic ( $T_j=125^\circ\text{C}$ )

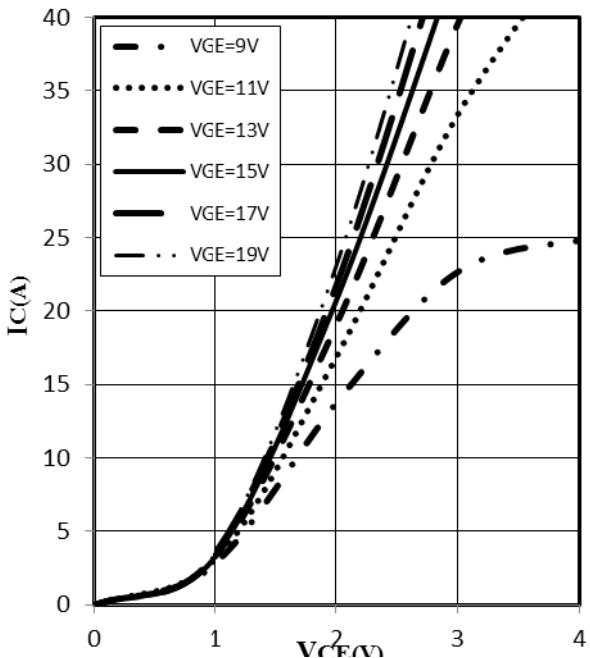


Fig 7. Typical transfer characteristic ( $V_{CE}=20\text{V}$ )

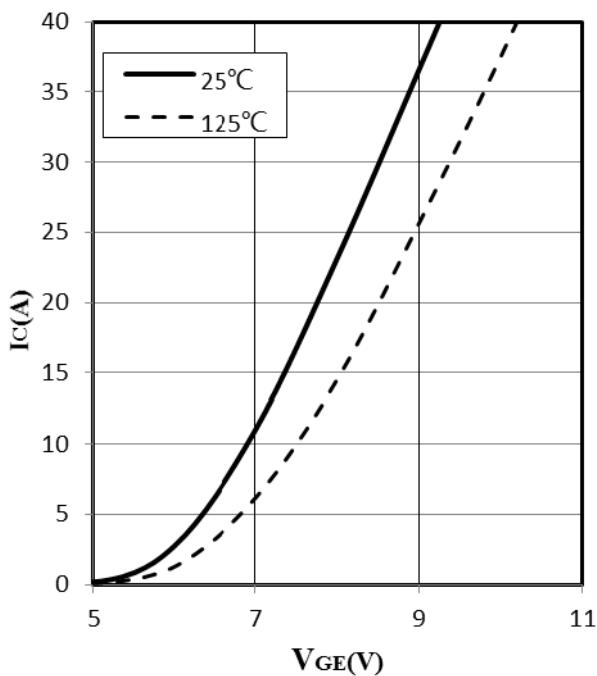
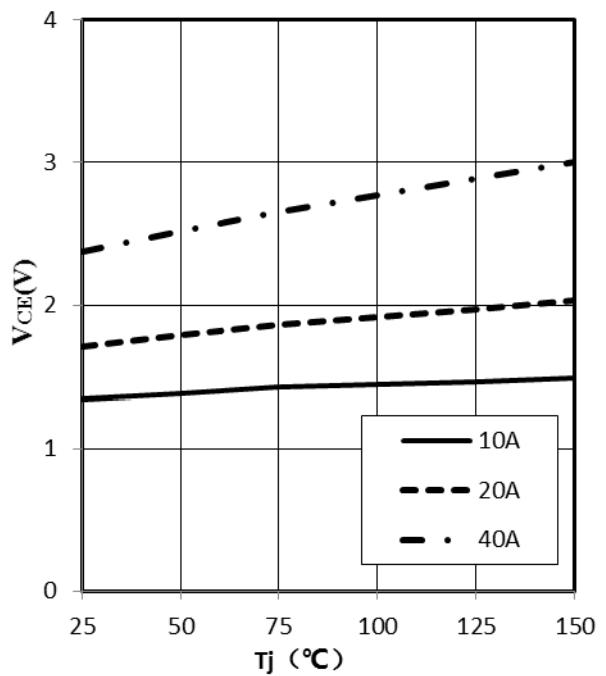


Fig 8. Typical collector-emitter saturation voltage as a function of junction temperature ( $V_{GE}=15\text{V}$ )



## Typical Characteristics

Fig 9. Typical collector-emitter saturation voltage as a function of  $V_{GE}$  ( $T_j=25^\circ C$ )

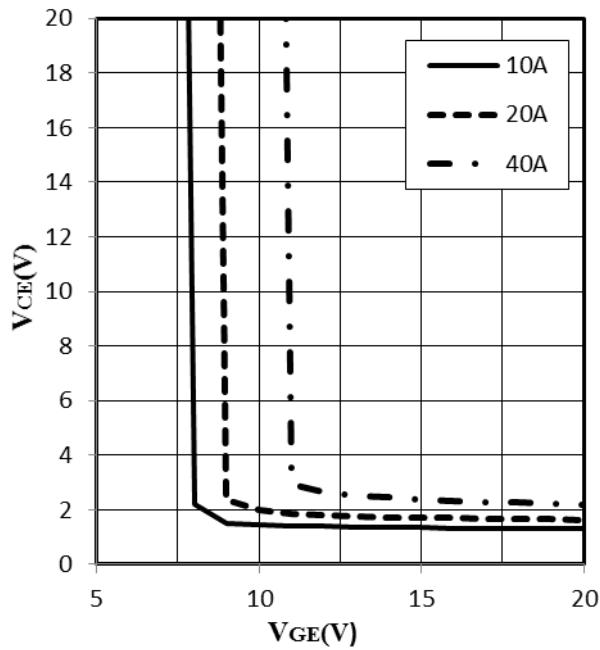


Fig 10. Typical collector-emitter saturation voltage as a function of  $V_{GE}$  ( $T_j=125^\circ C$ )

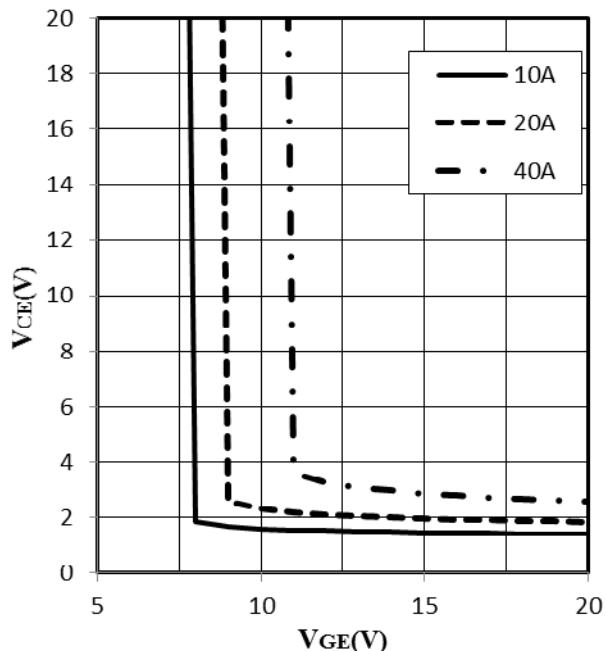


Fig 11. Typical switch energy as a function of  $I_c$   
(inductive load,  $T_j=25^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=15V$ ,  $R_G=10\Omega$ )

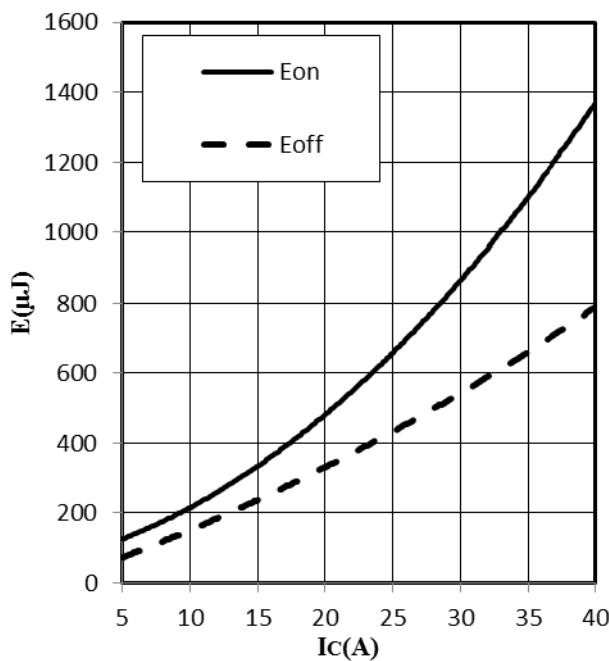
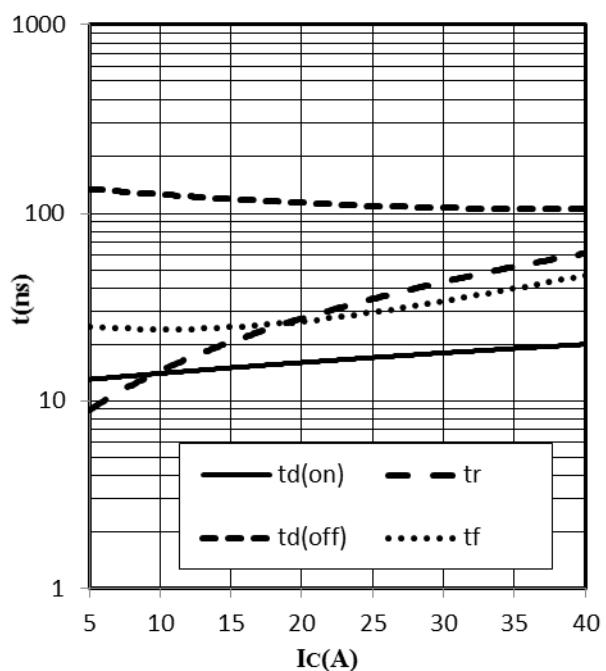


Fig 12. Typical switch time as a function of  $I_c$   
(inductive load,  $T_j=25^\circ C$ ,  $V_{CE}=400V$ ,  $V_{GE}=15V$ ,  $R_G=10\Omega$ )



## Typical Characteristics

Fig 13. Typical switch energy as a function of  $R_g$   
(inductive load,  $T_j=25^\circ\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=15\text{V}$ ,  $I_c=20\text{A}$ )

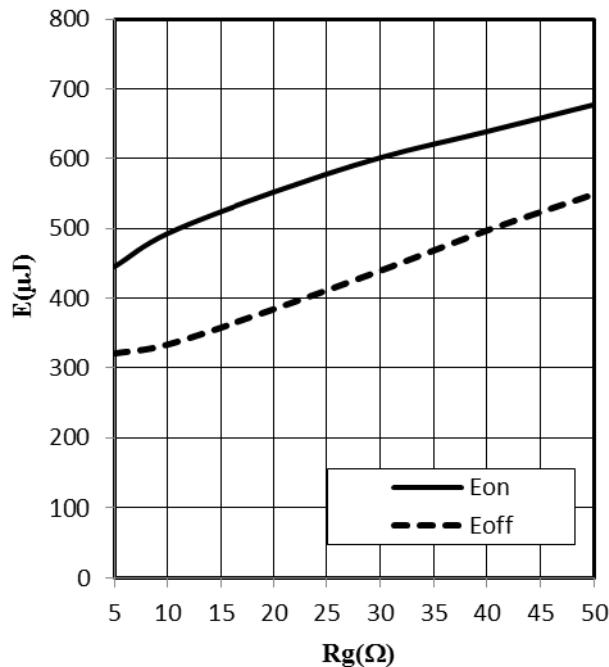


Fig 15. Typical capacitance as a function of collector-emitter voltage ( $V_{GE}=0\text{V}$ ,  $f=1\text{MHz}$ )

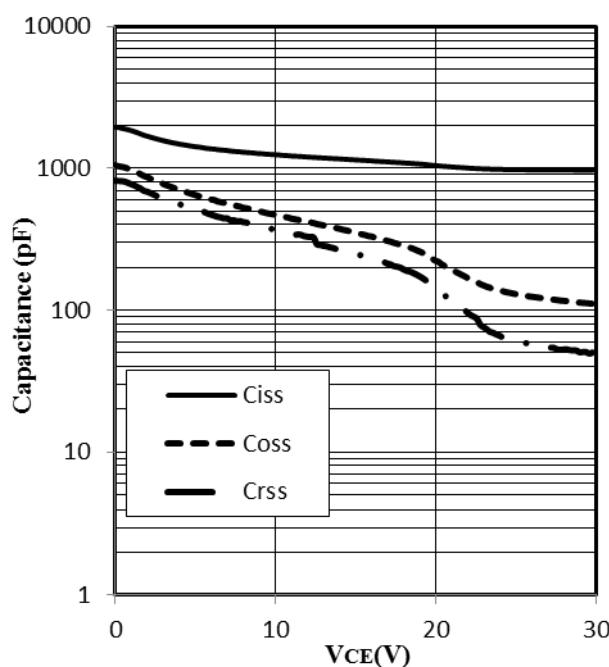


Fig 14. Typical switch time as a function of  $R_g$   
(inductive load,  $T_j=25^\circ\text{C}$ ,  $V_{CE}=400\text{V}$ ,  $V_{GE}=15\text{V}$ ,  $I_c=20\text{A}$ )

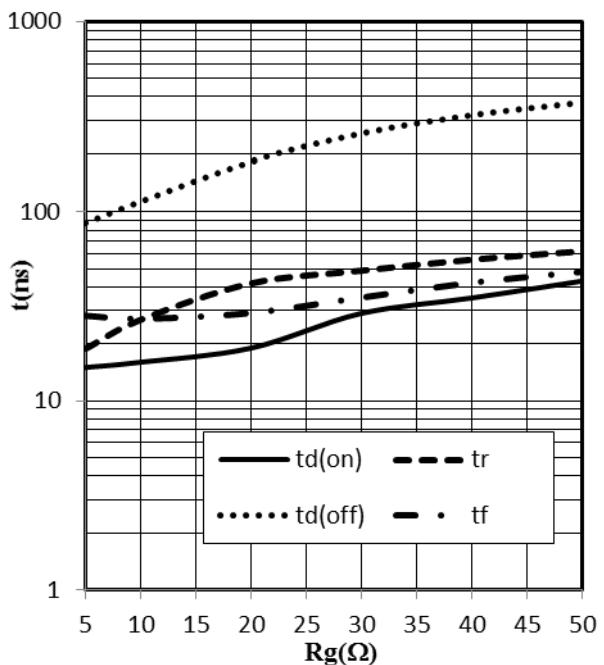
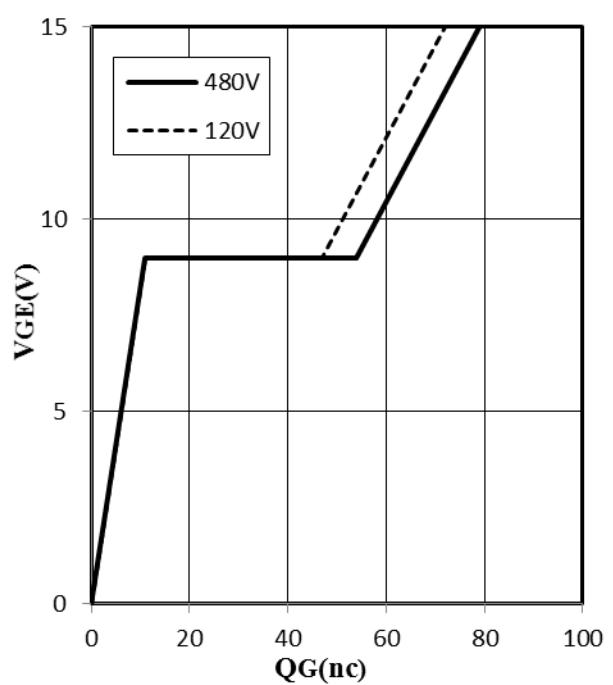


Fig 16. Typical gate charge ( $I_c=20\text{A}$ )



## Typical Characteristics

Fig 17. Typical diode forward current as a function of forward voltage

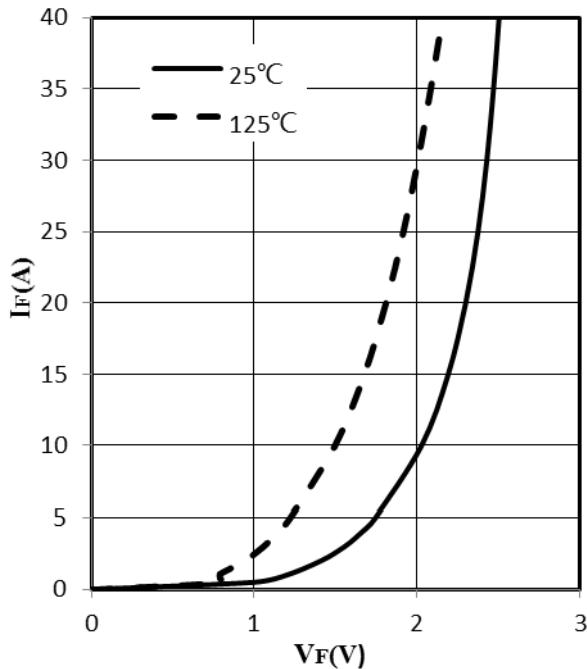


Fig 18. Typical trr as a function of dI<sub>F</sub>/dt

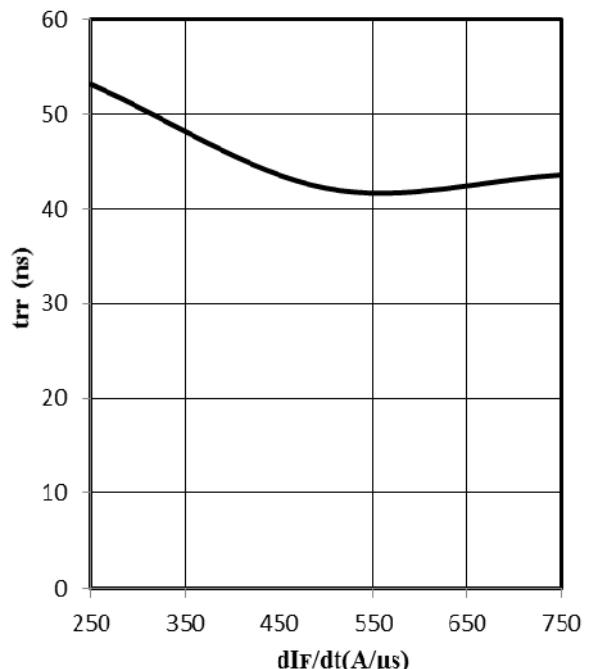


Fig 19. Typical I<sub>rrm</sub> as a function of dI<sub>F</sub>/dt

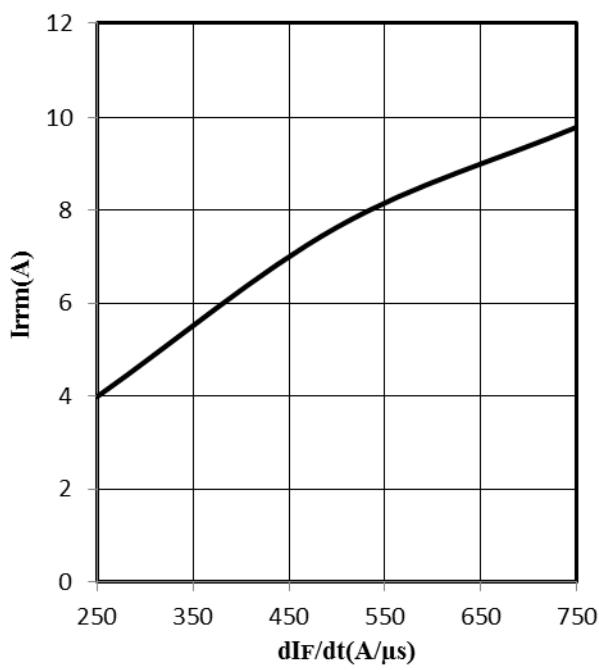
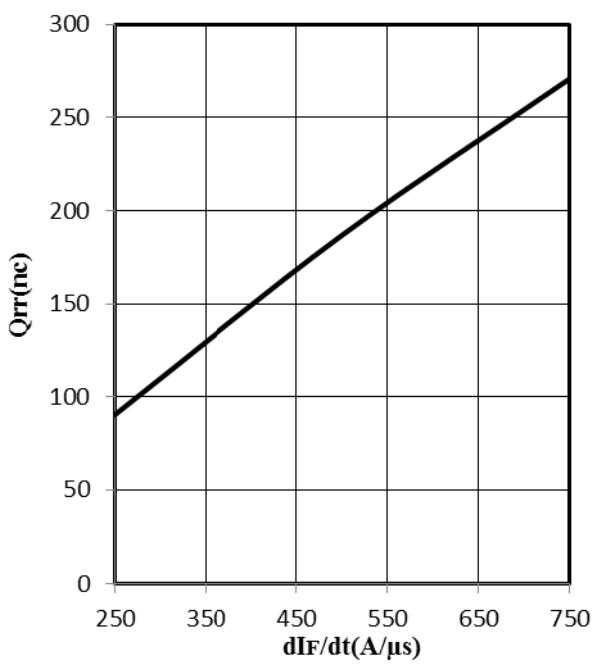
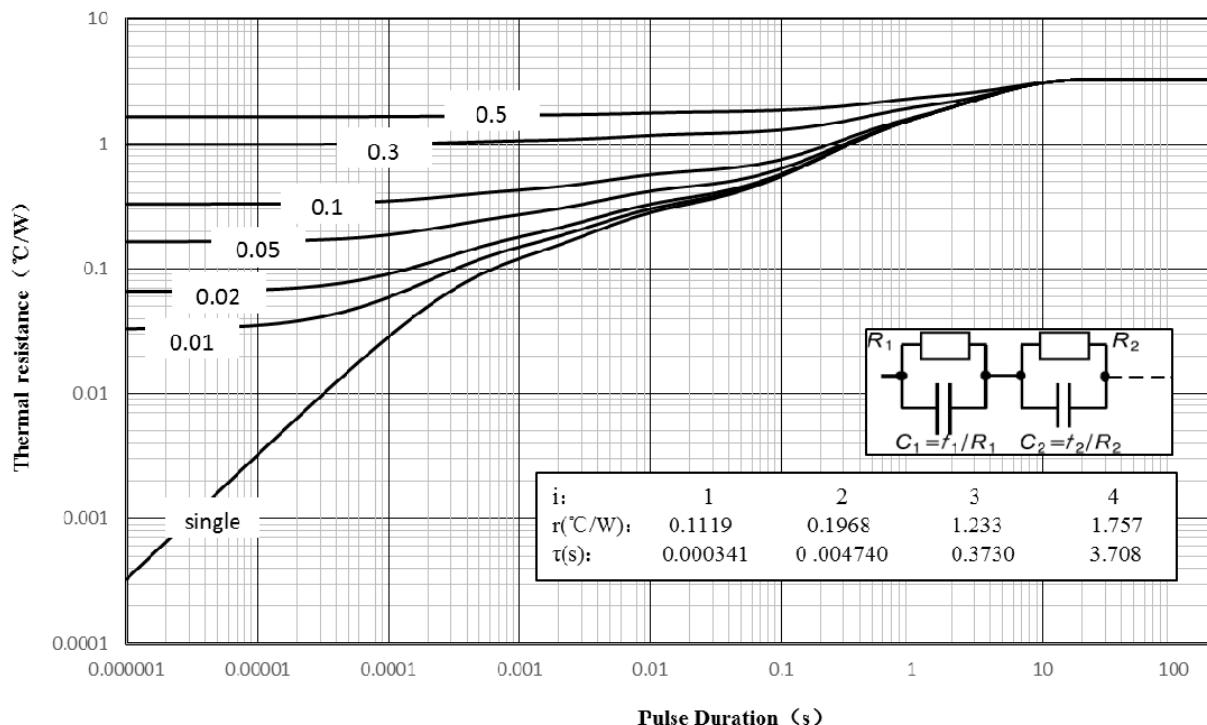


Fig 20. Typical Q<sub>rr</sub> as a function of dI<sub>F</sub>/dt

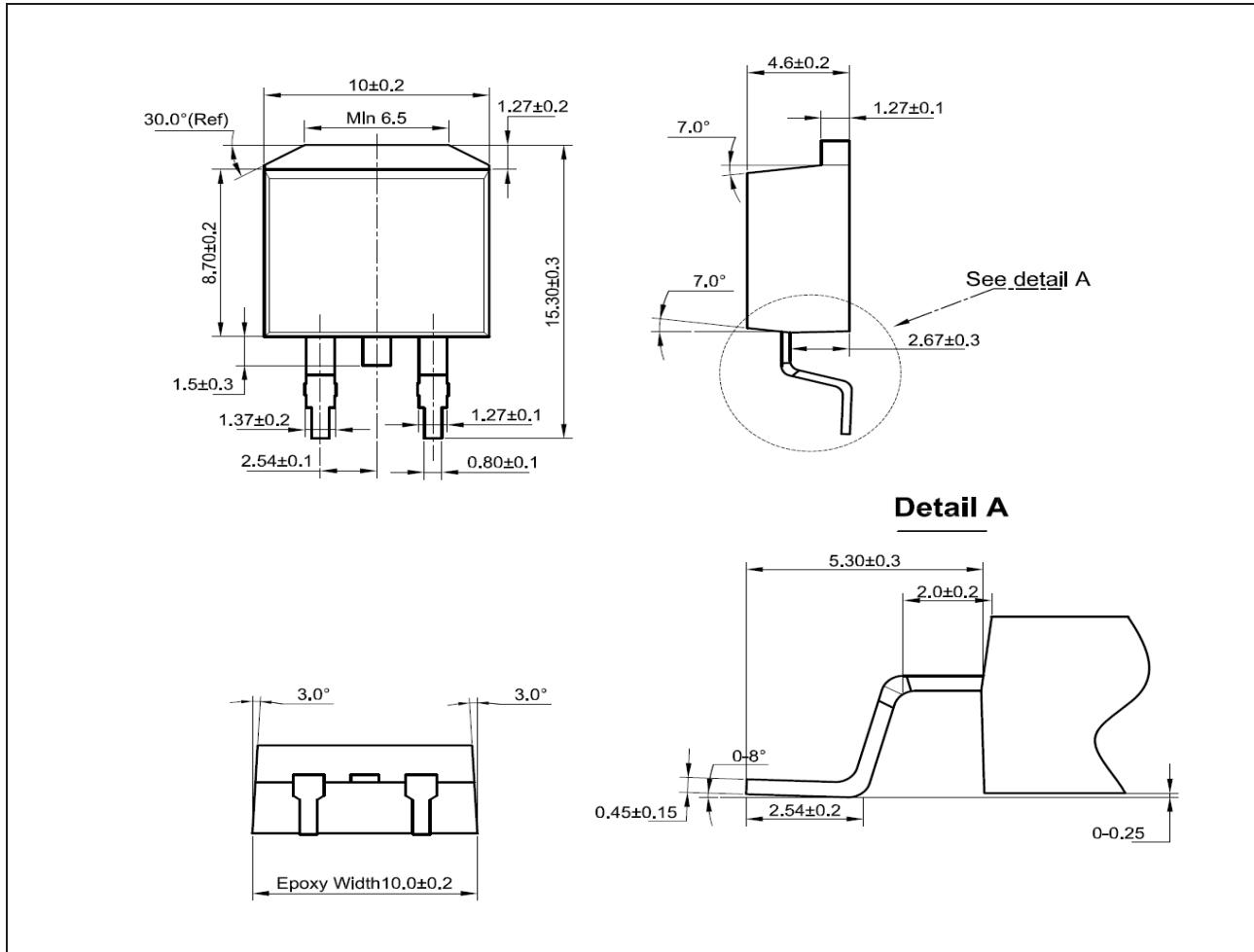


## Typical Characteristics

Fig 21. IGBT transient thermal resistance( $D=tp/T$ )



## Package Dimensions



## **Ordering information**

Order code	Package	Packaging option	Base quantity	Packaging specification
CXG20N65BS	TO-263	Tape/Reel	800pcs / Reel	EIA STD RS-481

## Revision history

Date	Revision	Changes
23-May-2018	1.0	Initial release

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